

January 2000 PRELIMINARY

FDS3680

100V N-Channel PowerTrench® MOSFET

General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

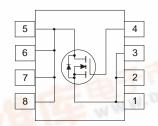
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{\text{DS(ON)}}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 5.2 A, 100 V. $R_{DS(ON)} = 0.043~\Omega~@~V_{GS} = 10~V$ $R_{DS(ON)} = 0.048~\Omega~@~V_{GS} = 6~V.$
- · Low gate charge.
- Fast switching speed
- High performance trench technology for extremely low R_{DS(ON)}.
- High power and current handling capability.





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{DSS}	Drain-Source Voltage		100	V
V _{GSS}	Gate-Source Voltage		±20	V
ID	Drain Current - Continuous	(Note 1a)	5.2	Α
	- Pulsed		50	- 17.11
P _D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	0750.0
		(Note 1c)	1.0	
T_J , T_{STG}	Operating and Storage Junction Tempera	ture Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
R _{eJC}	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS3680	FDS3680	13"	12mm	2500 units

Symbol	Parameter	Min	Тур	Max	Units	
Off Char	acteristics				I	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A,Referenced to 25°C		101		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			25	μΑ
I _{GSSF}	Gate–Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate–Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	2	2.4	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		-6.5		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$\begin{array}{cccccccccccccccccccccccccccccccccccc$		0.032 0.061	0.043 0.086	Ω
		$V_{GS} = 6 \text{ V}, \qquad I_{D} = 4.5 \text{ A}$	0.5	0.034	0.048	
D(on)	On–State Drain Current	$V_{GS} = 10 \text{ V}, \qquad V_{DS} = 5 \text{ V}$	25			A
g FS	Forward Transconductance	$V_{DS} = 5 \text{ V}, \qquad I_{D} = 5.2 \text{ A}$		25		S
	Characteristics	T.,			ı	
C _{iss}	Input Capacitance	$V_{DS} = 50 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		1735		pF
Coss	Output Capacitance	f = 1.0 MHz		176		pF
C _{rss}	Reverse Transfer Capacitance			53		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 50 \text{ V}, \qquad I_{D} = 1 \text{ A}, $ $V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 10 \Omega$		14	25	ns
t _r	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 10 \Omega$		8.5	17	ns
$t_{d(off)}$	Turn-Off Delay Time			63	94	ns
t _f	Turn-Off Fall Time			21	34	ns
Q_g	Total Gate Charge	$V_{DS} = 50 \text{ V}, \qquad I_{D} = 6 \text{ A},$		38	53	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 10 V		8.1		nC
Q_{gd}	Gate-Drain Charge			9.2		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
ls	Maximum Continuous Drain-Source				2.1	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 2.1 \text{ A} \text{(Note 2)}$		0.73	1.2	V

Notes:

 R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BCA} is determined by the user's board design.



a) 50°C/W when mounted on a 1in² pad of 2 oz copper



b) 105°C/W when mounted on a 0.04 in² pad of 2 oz



c) 125°C/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width < $300\mu s$, Duty Cycle < 2.0%

Typical Characteristics

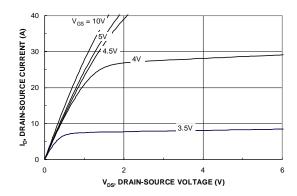


Figure 1. On-Region Characteristics.

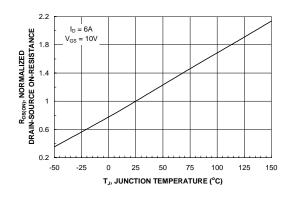


Figure 3. On-Resistance Variation withTemperature.

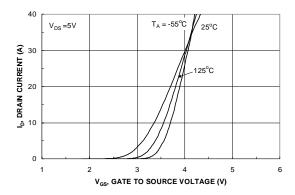


Figure 5. Transfer Characteristics.

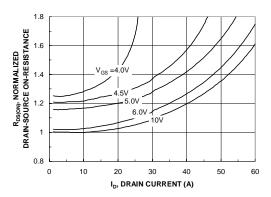


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

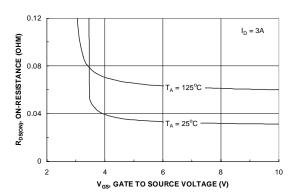


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

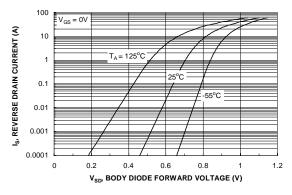
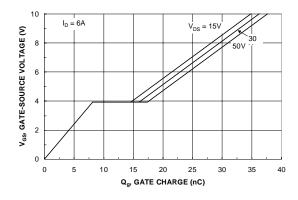


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



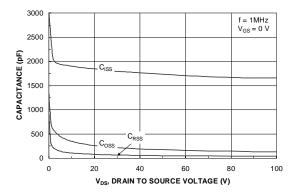


Figure 7. Gate Charge Characteristics.

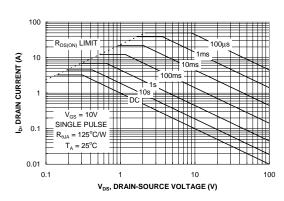


Figure 8. Capacitance Characteristics.

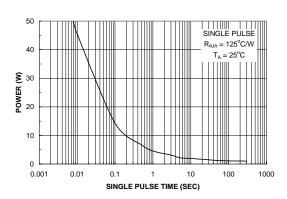


Figure 9. Maximum Safe Operating Area.



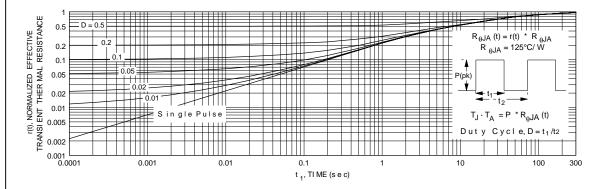
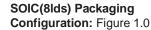


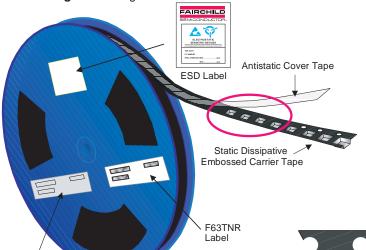
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient themal response will change depending on the circuit board design.

SO-8 Tape and Reel Data and Package Dimensions



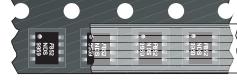




Packaging Description:

SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13° or 330m diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 500 units per 7° or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts





Packaging Option no flow code) Packaging type Rail/Tube TNR TNR Qty per Reel/Tube/Bag 2,500 95 4,000 500 Reel Size 13" Dia 13" Dia 7" Dia Box Dimension (mm) 343x64x343 530x130x83 343x64x343 184x187x47 Max qty per Box 5,000 30,000 8,000 1,000

SOIC (8lds) Packaging Information

Weight per unit (gm) 0.0774 0.0774 0.0774 0.0774 Weight per Reel (kg) 0.6060 0.9696 0.1182 Note/Comments

SOIC-8 Unit Orientation

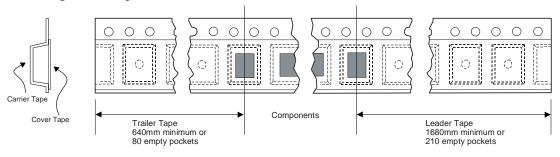
F63TNR Label sample

Customized



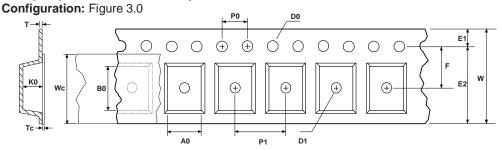
343mm x 342mm x 64mm Standard Intermediate box ESD Label F63TN Label

SOIC(8lds) Tape Leader and Trailer Configuration: Figure 2.0



SO-8 Tape and Reel Data and Package Dimensions, continued

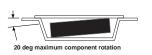
SOIC(8lds) Embossed Carrier Tape



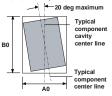
User Direction of Feed	
	$\overline{}$

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOIC(8lds) (12mm)	6.50 +/-0.10	5.30 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	2.1 +/-0.10	0.450 +/- 0.150	9.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



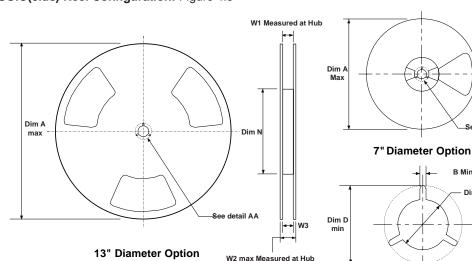
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

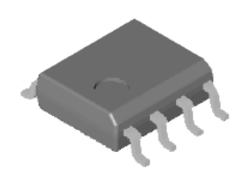
SOIC(8lds) Reel Configuration: Figure 4.0

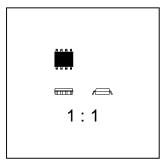


								DETAIL AA	
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

SO-8 Tape and Reel Data and Package Dimensions, continued

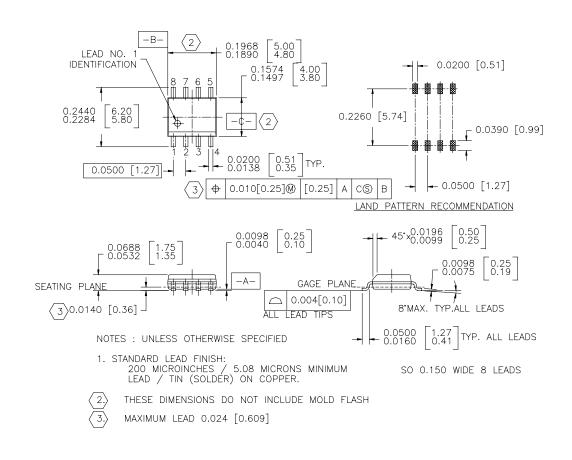
SOIC-8 (FS PKG Code S1)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0774



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